

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	0	takaishi near massaru.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 11:41
2	BRS	L2	35	takaishi near masaru.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 11:41
3	BRS	L3	5364	((silicon) near3 (thin or film)) near25 ((aluminum) near3 (thin or film))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 11:42

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	273	((silicon) near3 (thin or film)) near25 ((aluminum) near3 (thin or film)) near25 (contact near hole)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 11:47
5	BRS	L5	60	(remov\$3 or pattern\$3) near15 ((silicon) near3 (thin or film)) near25 ((aluminum) near3 (thin or film)) near25 (contact near hole)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 11:48
6	BRS	L7	24	(remov\$3 or pattern\$3) near15 ((silicon) near3 (thin or film)) near25 ((aluminum) near3 (thin or film)) near35 (heat\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 11:49

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L6	804	(remov\$3 or pattern\$3) near15 ((silicon) near3 (thin or film)) near25 ((aluminum) near3 (thin or film))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 12:08
8	BRS	L8	32073	(remov\$3 or pattern\$3) near15 ((silicon) near3 (thin or film))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 12:08
9	BRS	L9	18251	(remov\$3) near15 ((silicon) near2 (thin or film))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 12:10

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	25	(remov\$3) near15 ((silicon-containing) near (thin or film))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 12:09
11	BRS	L12	211	(remov\$3) near15 ((silicon) near2 (thin or film)) near25 (substrate) same (aluminum)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 12:18
12	BRS	L13	866	(remov\$3) near15 ((silicon) near2 (thin or film)) near25 (substrate) same (contact or hole)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 12:18

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L11	5948	(remov\$3) near15 ((silicon) near2 (thin or film)) near25 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 15:45
14	BRS	L14	1469	(la or aluminum) near25 (si or silicon) near25 (contact near hole)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 15:46
15	BRS	L15	2254	(al or aluminum) near25 (si or silicon) near25 (contact near hole)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 15:46

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	656	(al or aluminum) near25 (si or silicon) near25 (contact near hole) near25 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 16:18
17	BRS	L17	1685	(al or aluminum) near25 (si or silicon) near25 (diffus\$3) near25 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 16:19
18	BRS	L19	230	(heat\$3) near15 (al or aluminum) near25 (si or silicon) near25 (diffus\$3) near25 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 16:20

	Type	L #	Hits	Search Text	DBs	Time Stamp
19	BRS	L18	650	(heat\$3) near15 (al or aluminum) near25 (diffus\$3) near25 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 16:31
20	BRS	L20	14	(heat\$3) near15 (al or aluminum) near3 (thin near film) near25 (diffus\$3) near25 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 16:31
21	BRS	L21	53	(al or aluminum) near3 (thin near film) near25 (diffus\$3) near25 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/1 3 16:32

	U	1	Document ID	Title	Current OR
1	X		US 20040191996 A1	Method for manufacturing semiconductor device and semiconductor device	438/270
2	X		US 20040185660 A1	Method for manufacturing semiconductor device	438/688
3	X		US 20040185659 A1	Method for manufacturing semiconductor device	438/673
4	X		US 6406561 B1	One-step noble metal-aluminide coatings	148/242
5	X		US 4648691 A	Liquid crystal display device having diffusely reflective picture electrode and pleochroic dye	349/162
6	X		US 4177298 A	Method for producing an InSb thin film element	438/547
7	X		JP 2003051606 A	SUBSTRATE FOR THIN FILM FORMATION	
8	X		JP 02301132 A	FORMING METHOD FOR ALUMINUM DIFFUSED LAYER ON SEMICONDUCTOR SUBSTRATE	

	U	1	Document ID	Title	Current OR
9	X		JP 02265238 A	FORMATION OF ALUMINUM SELECTIVE DIFFUSION LAYER ON SILICON SUBSTRATE	
10	X		JP 01022036 A	SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF	
11	X		JP 62260358 A	SOI SUBSTRATE AND MANUFACTURE THEREOF	
12	X		JP 60127728 A	DIFFUSING METHOD OF ALUMINUM TO SEMICONDUCTOR	
13	X		JP 59084439 A	MANUFACTURE OF SEMICONDUCTOR DEVICE	
14	X		US 3680204 A	Solid state triode - has emitter, collector and control electrodes with body of material supporting emitter space-charge-limi	